

In the Claims:

Marked up version of once amended claim 24:

24. (Once Amended) A structure in a semiconductor chip, said structure comprising:

a first area of a dielectric, said first area of said dielectric having a first permeability;

a second area of said dielectric, said second area of said dielectric having a second permeability, said second permeability being higher than said first permeability;

a permeability conversion material interspersed within said second area of said dielectric, said permeability conversion material having a third permeability, said third permeability being greater than said first and said second permeabilities;

a conductor patterned in said second area of said dielectric.

Clean version of once amended claim 24:

24. A structure in a semiconductor chip, said structure comprising:

B3
a first area of a dielectric, said first area of said dielectric having a first permeability;

Sub C1
a second area of said dielectric, said second area of said dielectric having a second permeability, said second permeability being higher than said first permeability;

B3
cond

a permeability conversion material interspersed within said second area of said dielectric, said permeability conversion material having a third permeability, said third permeability being greater than said first and said second permeabilities;
a conductor patterned in said second area of said dielectric.

Please cancel claim 27.

Marked up version of once amended claim 28:

28. (Once Amended) The structure of claim [27] 24 wherein said permeability conversion material is selected from the group consisting of nickel, iron, nickel-iron alloy, and magnetic oxide.

Clean version of once amended claim 28:

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28. The structure of claim 24 wherein said permeability conversion material is selected from the group consisting of nickel, iron, nickel-iron alloy, and magnetic oxide.
